# PMPB10XNE

## 20 V, single N-channel Trench MOSFET

**30 November 2012** 

**Product data sheet** 

### 1. Product profile

#### 1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 1.2 Features and benefits

- 2.2 kV ESD protection
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated, 100% solderable side pads for optical solder inspection

#### 1.3 Applications

- Charging switch for portable devices
- DC-to-DC converters
- Power management in battery-driven portables
- Hard disk and computing power management

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	20	V
V <sub>GS</sub>	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-	12.9	Α
Static characte	Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 9 \text{ A}; T_j = 25 \text{ °C}$		-	10	14	mΩ

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.





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## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	D	drain	1 6	D I	
2	D	drain	7		
3	G	gate		Transparent top view	G + + + + + \
4	S	source			
5	D	drain			
6	D	drain		S 017aaa255	
7	D	drain			
8	S	source			

## 3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMPB10XNE	DFN2020MD-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220			

## 4. Marking

Table 4. Marking codes

Type number	Marking code
PMPB10XNE	1H

## 5. Limiting values

Table 5. Limiting values

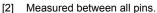
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	20	V
V <sub>GS</sub>	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	12.9	Α
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	9	Α
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	5.7	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	36	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[1]	-	1.7	W
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Symbol	Parameter	Conditions		Min	Max	Unit
		T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	3.5	W
		T <sub>sp</sub> = 25 °C		-	12.5	W
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain	diode					•
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	2	Α
ESD maximum rating						
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[2]	-	2200	V

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



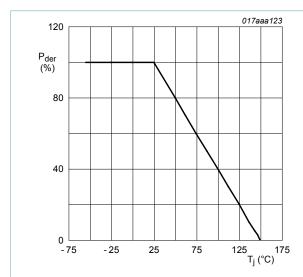


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

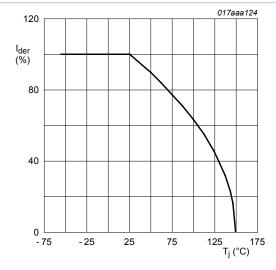


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

#### 20 V, single N-channel Trench MOSFET

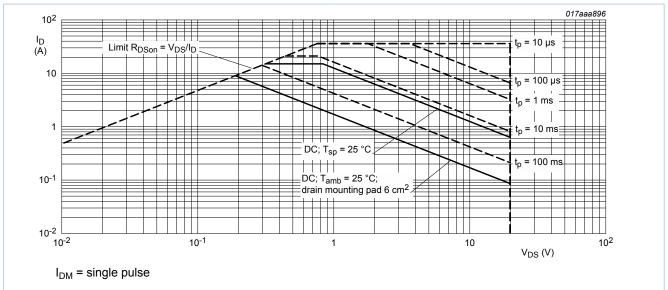


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

#### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
froi	thermal resistance	-	[1]	-	235	270	K/W
	from junction to ambient		<u>[2]</u>	-	67	74	K/W
	ambient	in free air; t ≤ 5 s	<u>[2]</u>	-	33	36	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	5	10	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

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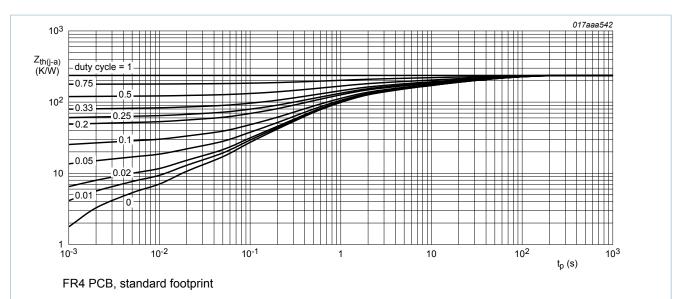


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

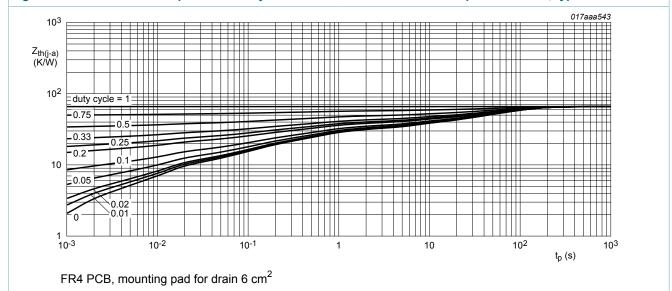


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

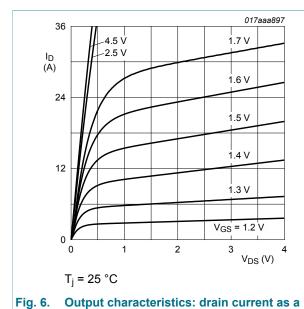
#### 7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static chara	Static characteristics						
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C		20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$		0.4	0.65	0.9	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$		-	-	1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	-	10	μΑ
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-10	μA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = 4.5 V; $I_D$ = 9 A; $T_j$ = 25 °C	-	10	14	mΩ
	resistance	$V_{GS}$ = 4.5 V; $I_{D}$ = 9 A; $T_{j}$ = 150 °C	-	15	21	mΩ
		$V_{GS}$ = 2.5 V; $I_D$ = 8 A; $T_j$ = 25 °C	-	12	18	mΩ
		$V_{GS}$ = 1.8 V; $I_{D}$ = 3.7 A; $T_{j}$ = 25 °C	-	16	25	mΩ
g <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 9 A; T <sub>j</sub> = 25 °C	-	60	-	S
$R_G$	gate resistance	f = 1 MHz	-	2	-	Ω
Dynamic c	haracteristics			'		'
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 10 V; $I_{D}$ = 6 A; $V_{GS}$ = 4.5 V; $T_{j}$ = 25 °C	-	23	34	nC
$Q_{GS}$	gate-source charge		-	2.6	-	nC
$Q_{GD}$	gate-drain charge		-	4.5	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = 10 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	2175	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	235	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	205	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 10 \text{ V}; I_D = 6 \text{ A}; V_{GS} = 4.5 \text{ V};$	-	13	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega$ ; $T_j = 25 °C$	-	35	-	ns
$t_{d(off)}$	turn-off delay time		-	54	-	ns
t <sub>f</sub>	fall time		-	50	-	ns
Source-dra	nin diode					
V <sub>SD</sub>	source-drain voltage	$I_S = 2 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.6	1.2	V
		1			1	



function of drain-source voltage; typical values

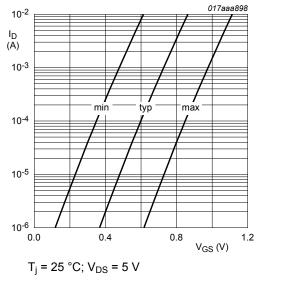


Fig. 7. Subthreshold drain current as a function of gate-source voltage

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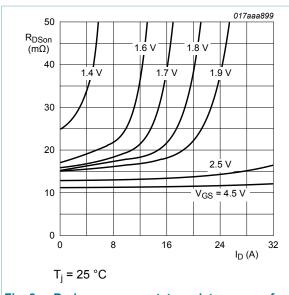


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

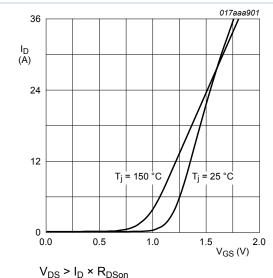


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

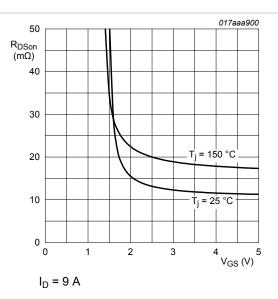


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

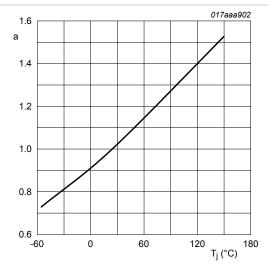


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

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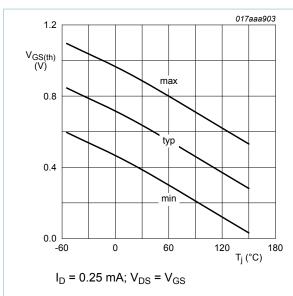


Fig. 12. Gate-source threshold voltage as a function of junction temperature

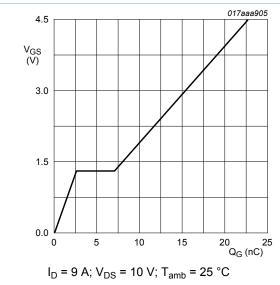


Fig. 14. Gate-source voltage as a function of gate charge; typical values

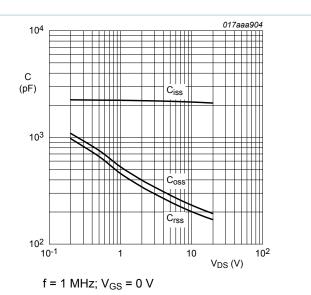


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

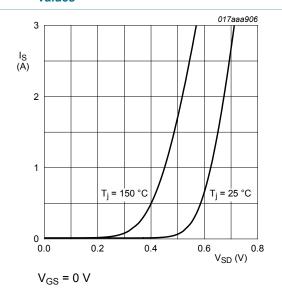
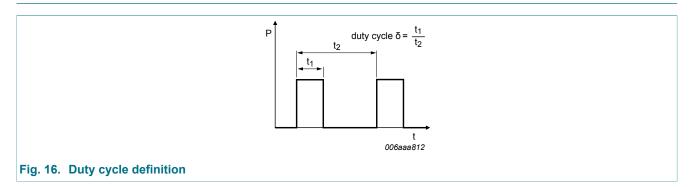


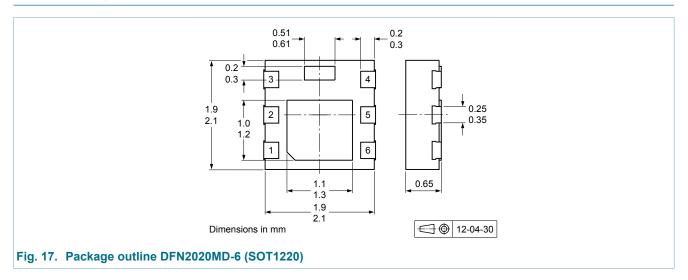
Fig. 15. Source current as a function of source-drain voltage; typical values

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### 8. Test information

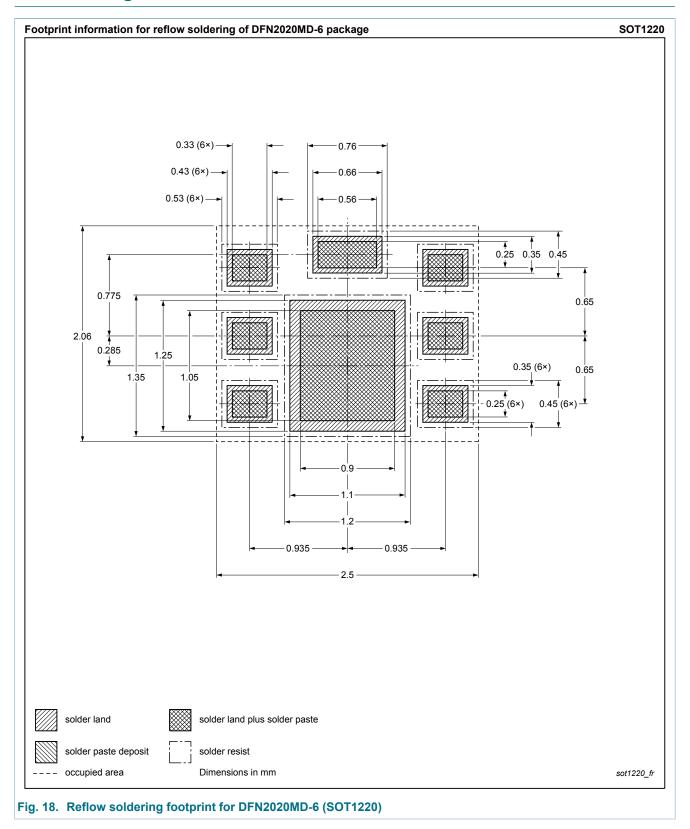


## 9. Package outline



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### 10. Soldering



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## 11. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB10XNE v.1	20121130	Product data sheet	-	-

#### 20 V, single N-channel Trench MOSFET

### 12. Legal information

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